

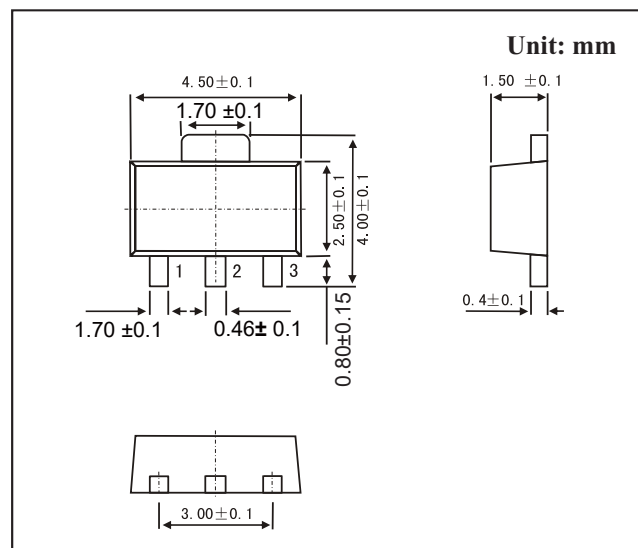
SOT-89 Plastic-Encapsulate Transistors

FEATURES

- High voltage
- High Transition Frequency
- Small Flat Package
- Complementary to KTC4373
- TRANSISTOR (PNP)

MECHANICAL DATA

- Case style:SOT-89 molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-120	V
Collector - Emitter Voltage	V_{CEO}	-120	
Emitter - Base Voltage	V_{EBO}	-5	
Collector Current - Continuous	I_C	-800	mA
Base Current	I_B	-160	
Collector Power Dissipation	P_C	500	mW
		1	W
Junction Temperature	T_J	150	°C
Storage Temperature range	T_{stg}	-55 to 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	$I_C = -1mA, I_E = 0$	-120			V
Collector- emitter breakdown voltage	V_{CEO}	$I_C = -10mA, I_B = 0$	-120			
Emitter - base breakdown voltage	V_{EBO}	$I_E = -1mA, I_C = 0$	-5			
Collector-base cut-off current	I_{CBO}	$V_{CB} = -120V, I_E = 0$			-100	nA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-100	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500mA, I_B = -50mA$			-1	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -500mA, I_B = -50mA$			-1.2	
Base - emitter voltage	V_{BE}	$V_{CE} = -5V, I_C = -500mA$			-1	
DC current gain	h_{FE}	$V_{CE} = -5V, I_C = -100mA$	80		240	
Collector output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$			30	pF
Transition frequency	f_T	$V_{CE} = -5V, I_C = -100mA$		120		MHz

RATINGS AND CHARACTERISTIC CURVES

